

Product Summary (Typ. @ $V_{GS} = -4.5V$, $T_A = +25^{\circ}C$)

BV_{DSS}	$R_{DS(ON)}$	Q_g	Q_{gd}	I_D
-25V	33m Ω	4.8nC	1.0nC	-5.2A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

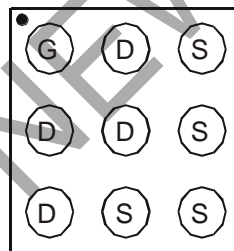
- Battery managements
- Load switches
- Battery protections

Features and Benefits

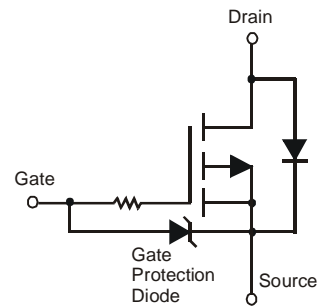
- LD-MOS Technology with the Lowest Figure of Merit:
 $R_{DS(ON)} = 33m\Omega$ to Minimize On-State Losses
 $Q_g = 4.8nC$ for Ultra-Fast Switching
- $V_{GS(th)} = -0.6V$ Typ. for a Low Turn-On Potential
- CSP with Footprint 1.5mm x 1.5mm
- Height = 0.62mm for Low Profile
- ESD = 6kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: U-WLB1515-9
- Terminal Connections: See Diagram Below
- Weight: 0.0018 grams (Approximate)



Top-View
Pin Configuration



Equivalent Circuit

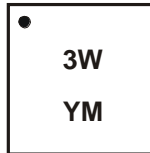
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP2540UCB9-7	U-WLB1515-9	3,000	Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

U-WLB1515-9



3W = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: J = 2022)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	...	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Y	...	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-25	V
Gate-Source Voltage	V _{GSS}	-6	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	I _D	Steady State T _A = +25°C	-4.0
		T _A = +70°C	-3.0
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	Steady State T _A = +25°C	-5.2
		T _A = +70°C	-4.0
Pulsed Drain Current (Pulse Duration 10μs, Duty Cycle ≤1%)	I _{DM}	-30	A
Continuous Source Pin Current (Note 6)	I _S	-2.0	A
Pulsed Source Pin Current (Pulse Duration 10μs, Duty Cycle ≤1%)	I _{SM}	-15	A
Continuous Gate Clamp Current (Note 5)	I _G	-0.6	A
Pulsed Gate Clamp Current (Pulse Duration 10μs, Duty Cycle ≤1%)	I _{GM}	-8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.0	W
Total Power Dissipation (Note 6)	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	126.8	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	69	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
 6. Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-25	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	-100	nA	V _{GS} = -6V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.6	-1.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	33	40	mΩ	V _{GS} = -4.5V, I _D = -2A
			42	50		V _{GS} = -2.5V, I _D = -2A
			52	60		V _{GS} = -1.8V, I _D = -2A
Forward Transfer Admittance	Y _{fs}	-	12	-	S	V _{DS} = -10V, I _D = -2A
Diode Forward Voltage (Note 5)	V _{SD}	-	-0.7	-1	V	V _{GS} = 0V, I _S = -2A
Reverse Recovery Charge	Q _{rr}	-	100	-	nC	V _{dd} = -9.5V, I _F = -2A, di/dt = 200A/μs
Reverse Recovery Time	t _{rr}	-	130	-	ns	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	342	450	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	174	225	pF	
Reverse Transfer Capacitance	C _{rss}	-	70	90	pF	
Series Gate Resistance	R _G	-	28	35	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	-	4.8	6.0	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -2A
Gate-Source Charge	Q _{gs}	-	0.5	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	11	-	ns	V _{DD} = -10V, V _{GS} = -4.5V, I _{DS} = -2A, R _G = 2Ω
Turn-On Rise Time	t _r	-	12	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	56	-	ns	
Turn-Off Fall Time	t _f	-	42	-	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN

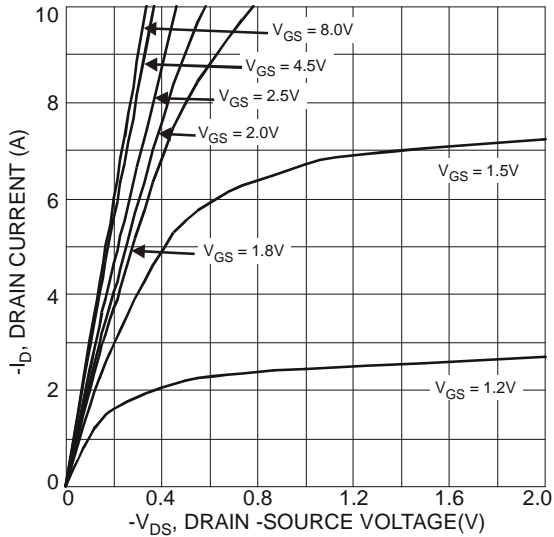


Fig. 1 Typical Output Characteristics

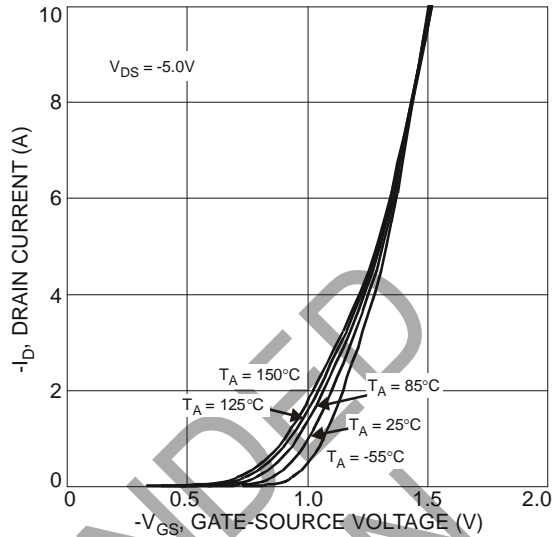


Fig. 2 Typical Transfer Characteristics

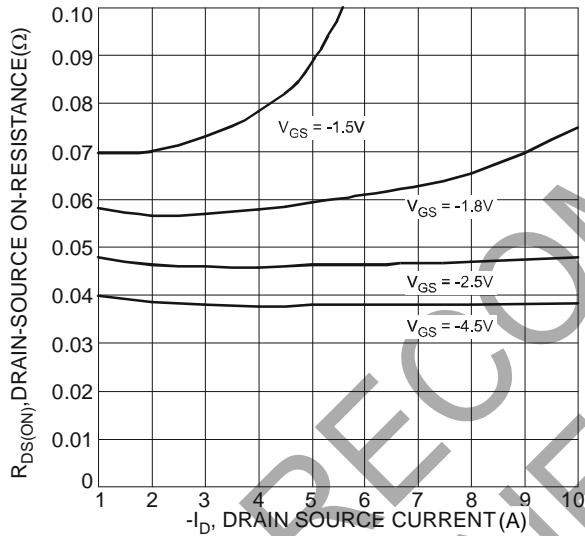


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

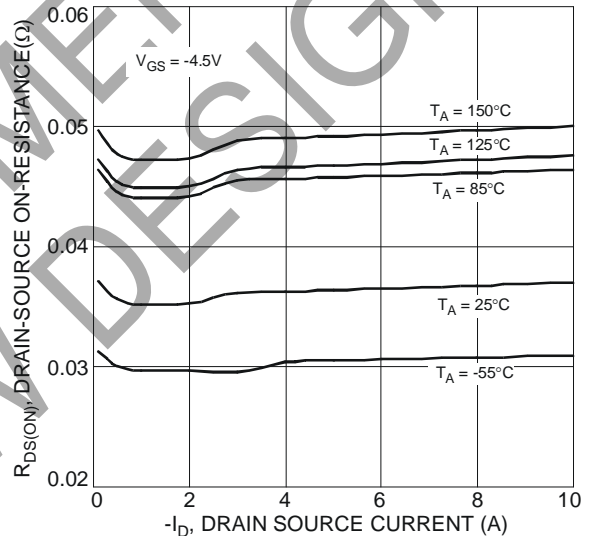


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

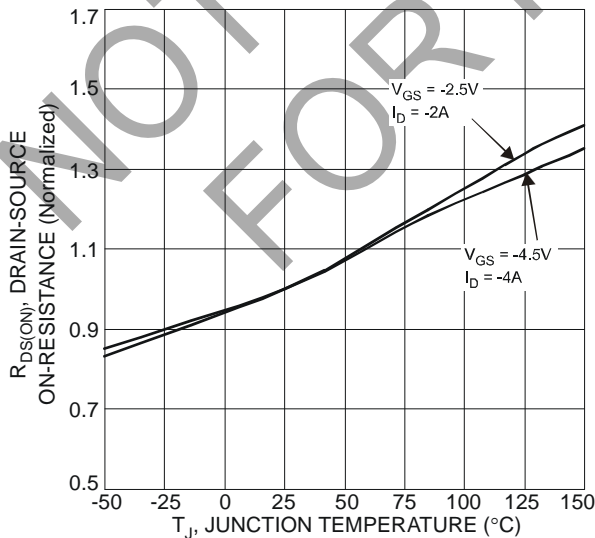


Fig. 5 On-Resistance Variation with Temperature

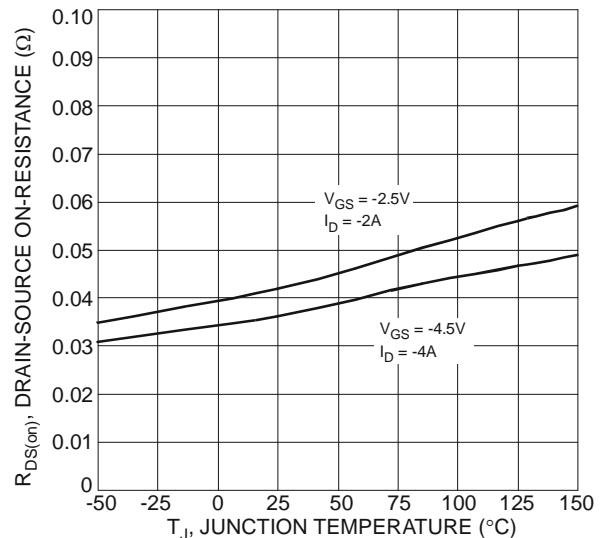


Fig. 6 On-Resistance Variation with Temperature

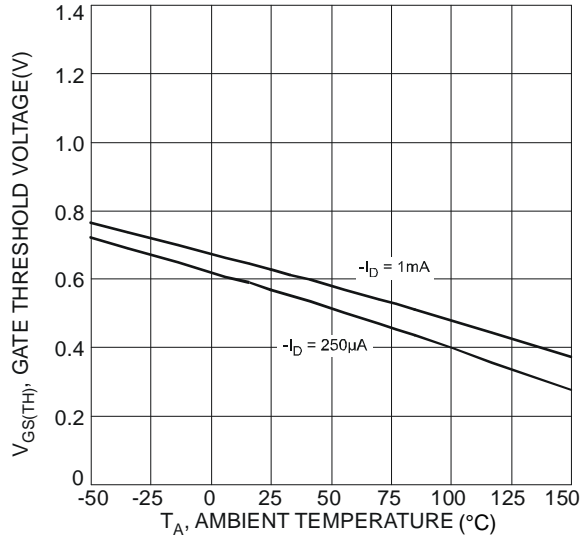


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

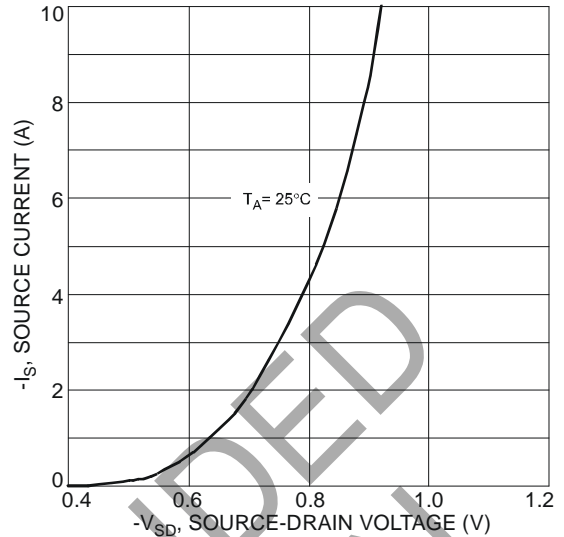


Fig. 8 Diode Forward Voltage vs. Current

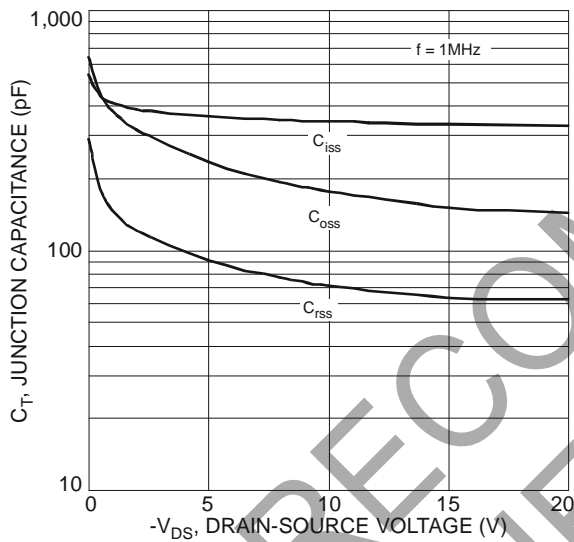


Fig. 9 Typical Junction Capacitance

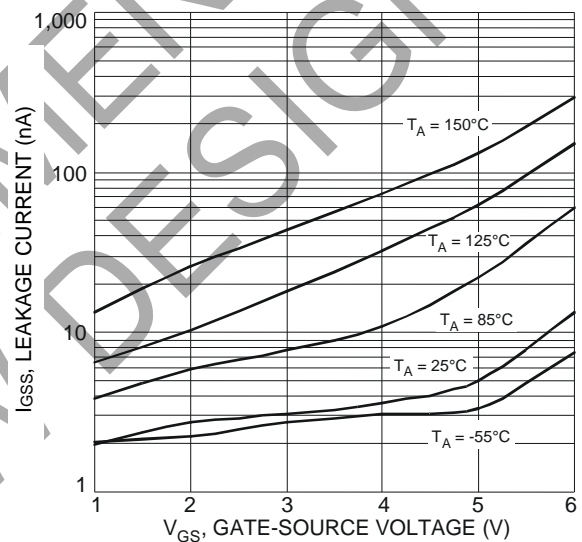


Fig. 10 Gate-Source Leakage Current vs. Voltage

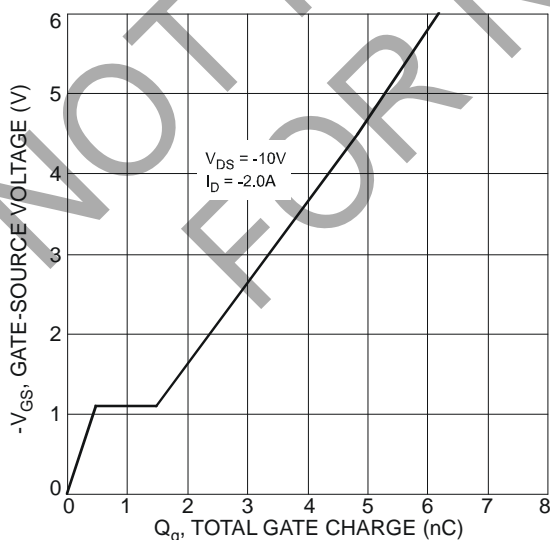


Fig. 11 Gate-Charge Characteristics

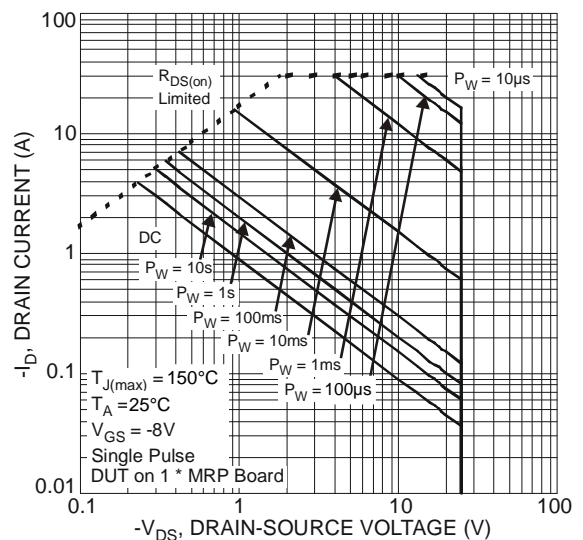
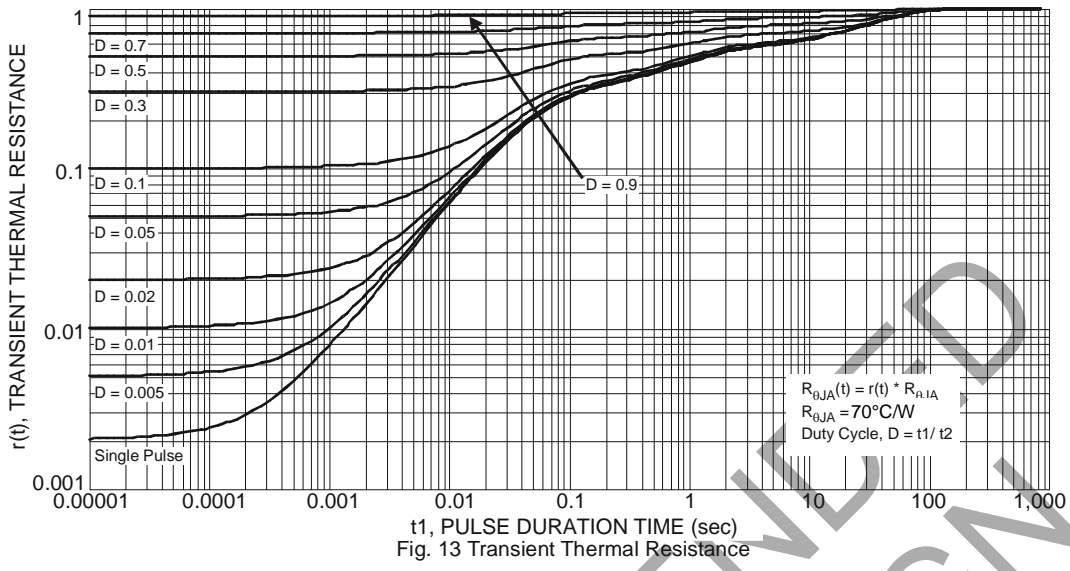


Fig. 12 SOA, Safe Operation Area

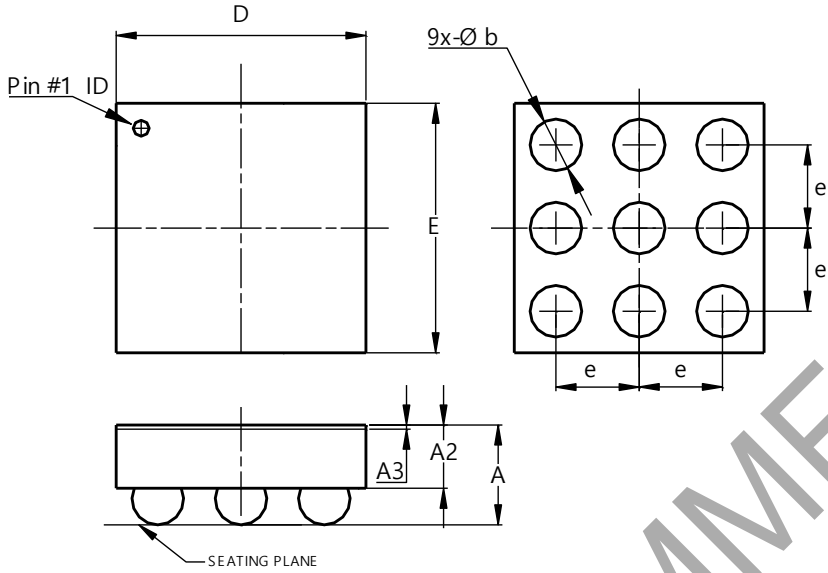


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Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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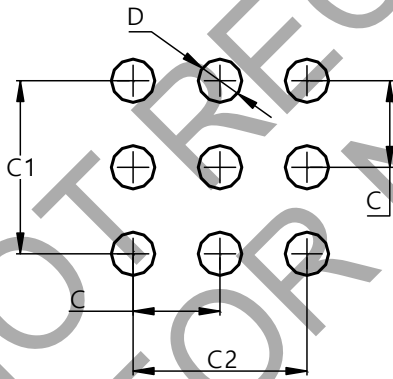


U-WLB1515-9			
Dim	Min	Max	Typ
A	--	0.62	--
A2	--	0.36	0.36
A3	0.020	0.030	0.025
b	0.27	0.37	0.32
D	1.47	1.50	1.49
E	1.47	1.50	1.49
e	--	--	0.50
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-WLB-1515-9



Dimensions	Value (in mm)
C	0.50
C1	1.00
C2	1.00
D	0.25

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